



GaN is widening the applications field in power electronics

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Energy transition

Resources are a common asset...



Reduce greenhouse gas emission

- **Transport:** automotive, space & aeronautics,
- **Industry:** pumps, motors, air-conditioning, multimodal energy approach
- **Digitalization:** massive data and « real time » calculation, data server, IA, ...

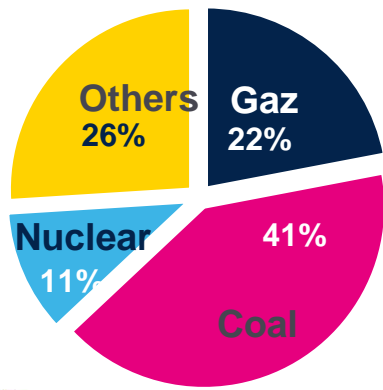
➔ « Fossil » energy to be massively reduced

Optimize all usage

- **Electrical power is also scarce**
- From production to...
- Recycling & upcycling

Energy saving with WBG* deployment

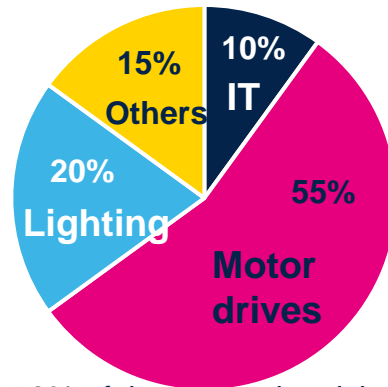
Electricity generation



World - 25000 TWh/Y (2021**)

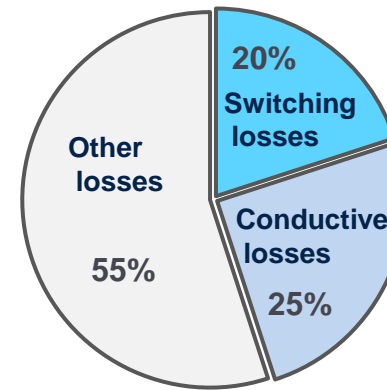
■ Gaz ■ Coal

Electricity usage



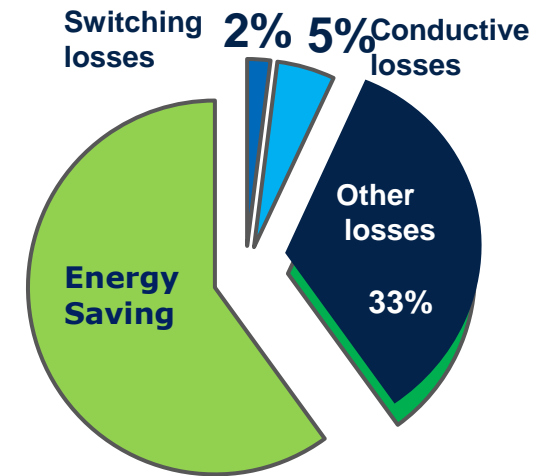
70% of the world electricity is managed by power electronics

Silicon technology



Total efficiency < 85%

WBG technology



Total efficiency > 95%

* Wide bandgap
** www.iea-4e.org

3 to 7% global energy-saving estimated through deployment of WBG

SiC and GaN semiconductors: enabling energy-efficient applications

Wide-bandgap semiconductors offer superior benefits and characteristics, thanks to:

Faster switching

Lower switching losses and higher efficiency

Higher switching frequencies

Smaller passive components

Higher operating voltages with low on-resistance

Reduced currents and lower conduction losses

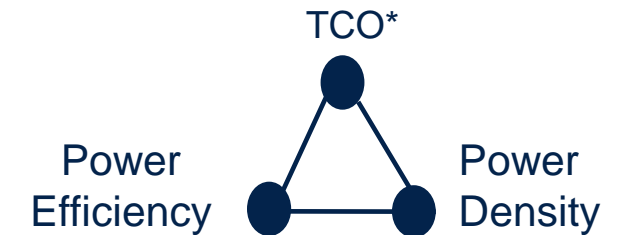
Higher junction temperatures

Reduced cooling requirement

Higher power densities

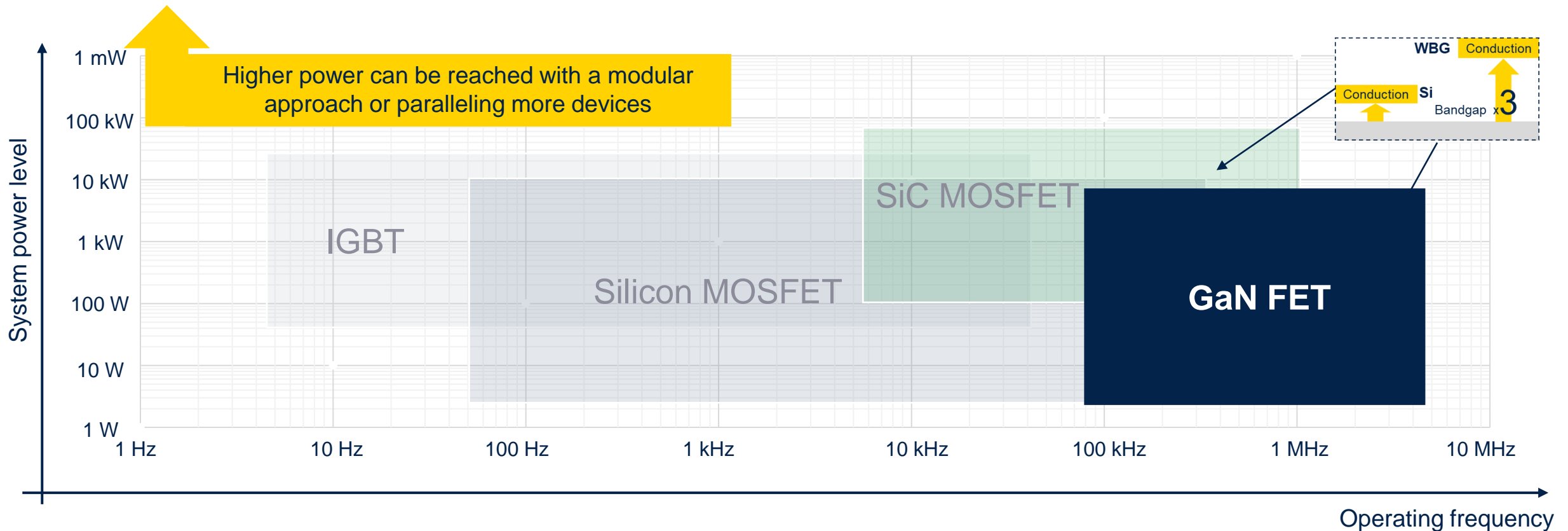
Miniaturization

New paradigm with WBG



Silicon, SiC, and GaN mapping as of today

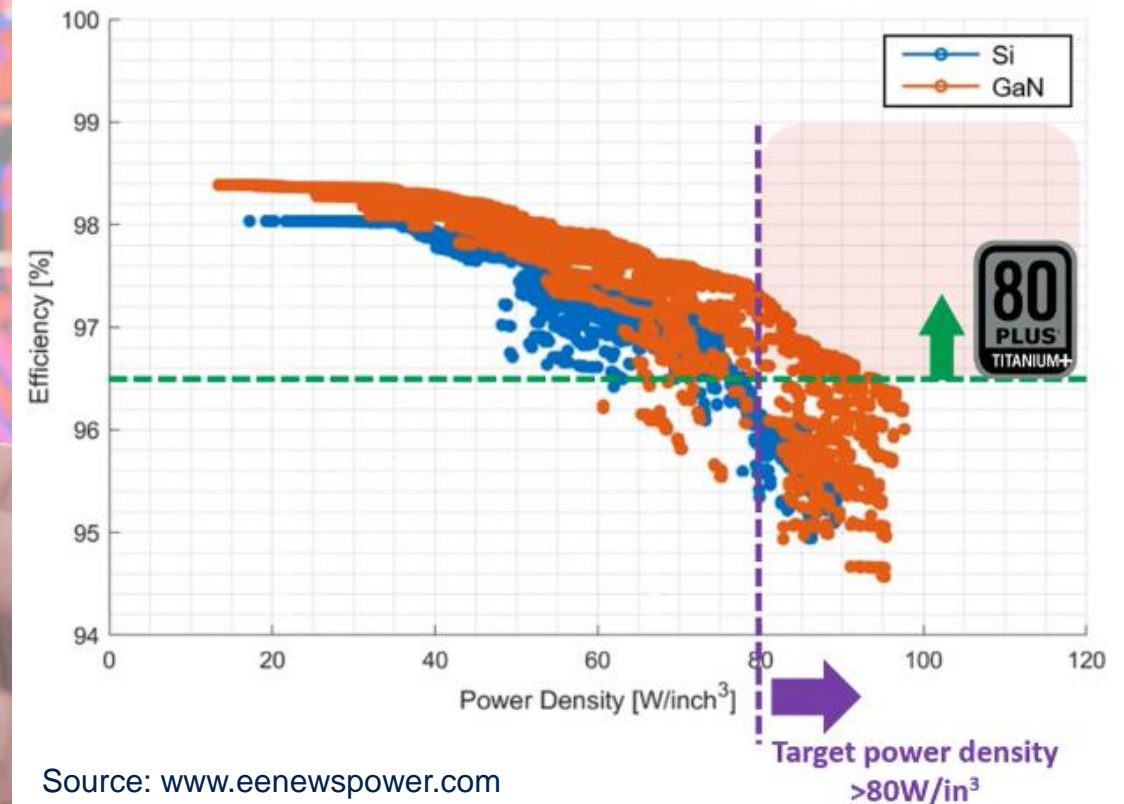
Silicon and wide bandgap materials are complementary



GaN can help meet growing power density needs for AI datacenters

By 2027, annual worldwide AI-related electricity consumption may rise by 85 to 134 TWh based on the projected AI server production

Highest efficiency
Smallest solutions
Reduces energy needs
Lowers CO2 emissions

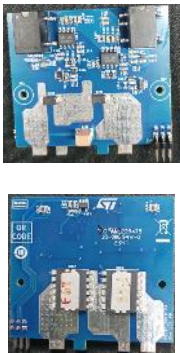
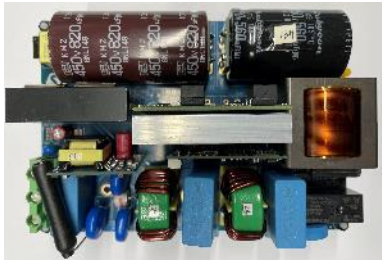


SiC/GaN boost efficiency and power density for AI server/datacenter

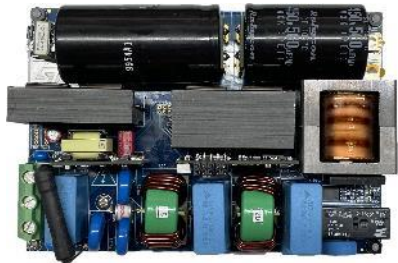
3 kW totem pole PFC with SiC or GaN

ST **Power GaN** to boost efficiency (100 x 145 x 40 mm)

GaN

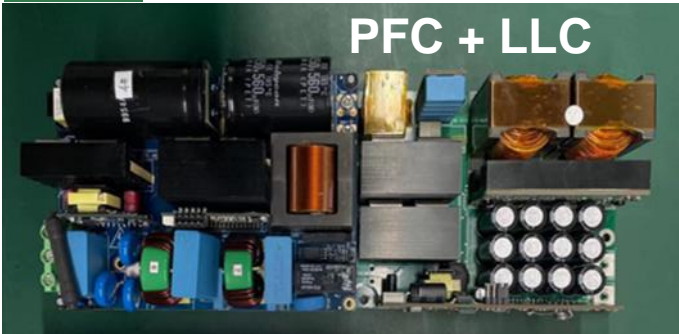


SiC MOSFET



3 kW totem pole PFC + LLC with GaN

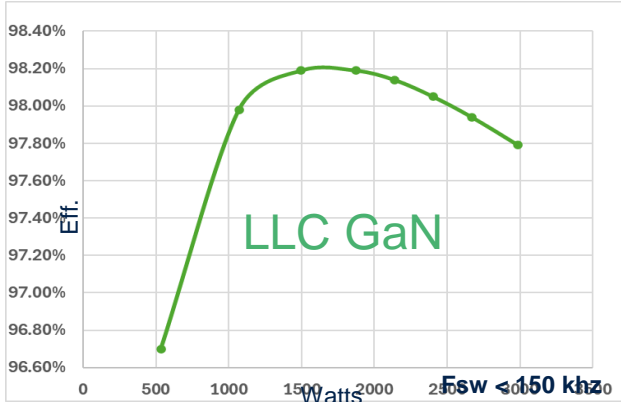
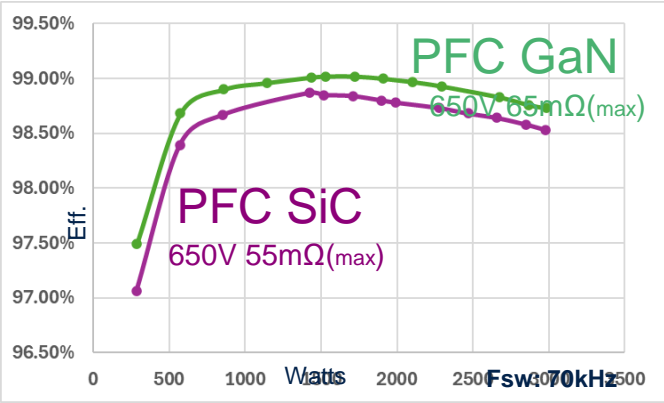
GaN



73.5 x 265 x 40 mm



PFC	SiC MOSFET		GaN
Power density (w/inch³)	85	x1	85
Power rating	3 kW	x1	3 kW
Peak eff. at 230Vac	98.5%	+0.5%	99%



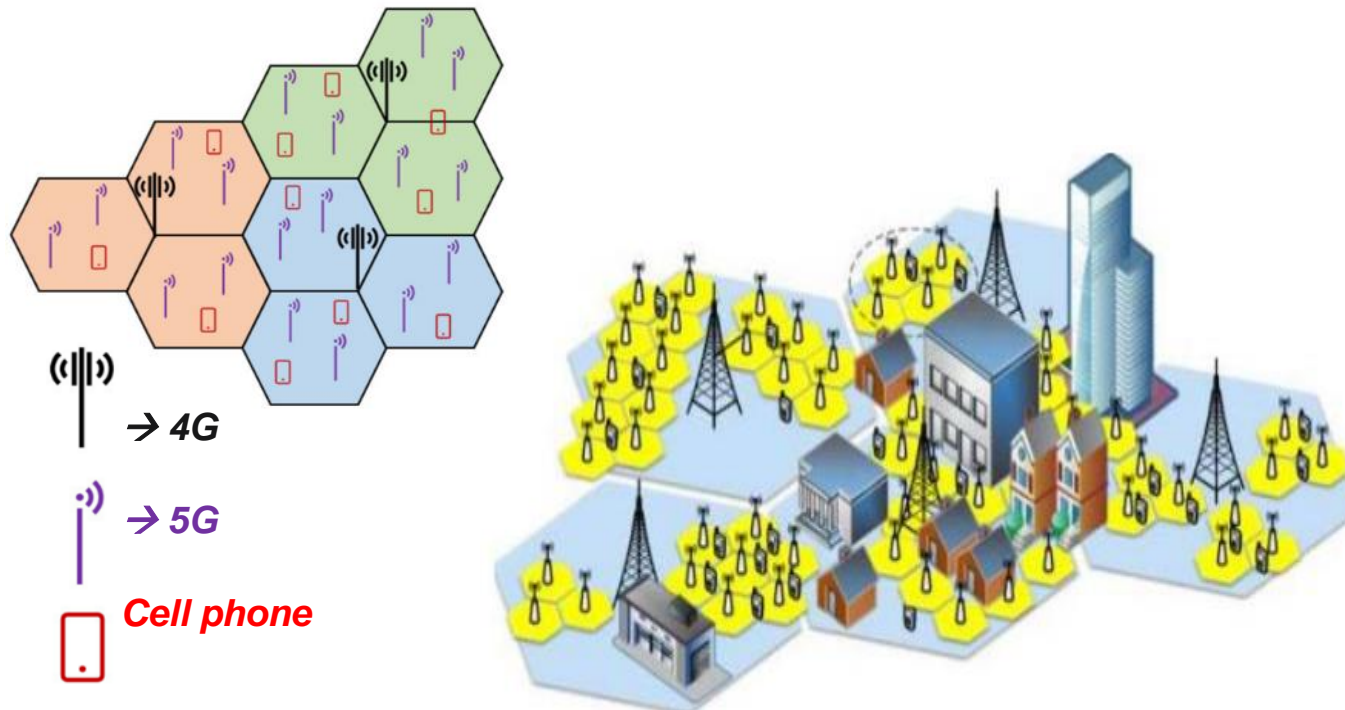
PFC+LLC	Si MOSFET		GaN
Power density (w/inch³)	45	X1.5	89
Power rating	2 kW	X1.5	3 kW
Peak eff. at 230Vac	95.28%	+1.94 %	97.22%

Higher system integration for 5G telecom power

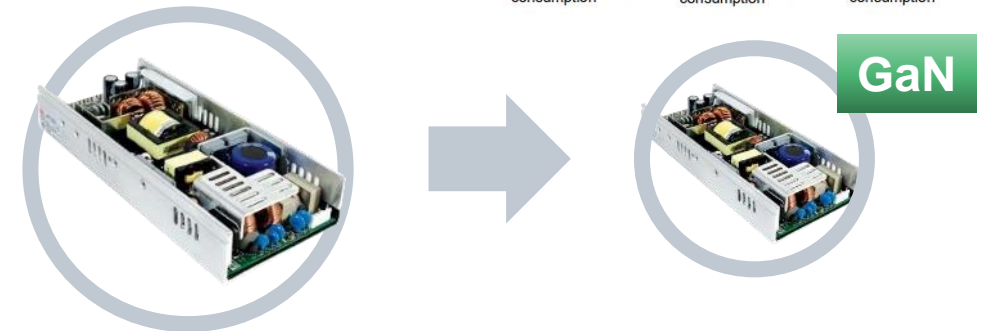
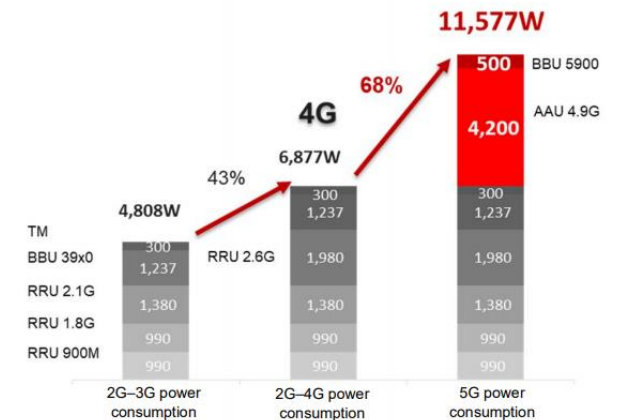
Enabling higher power density and higher efficiency

Smaller coverage due to higher frequency radio:
to achieve high network speed and low latency

Higher power consumption in 5G usage: to fulfill
high traffic density and connection density



Source: Huawei



Challenges for the grid

How to optimize investment in **energy transmission** upgrades?



How to manage **peak loads** that are becoming increasingly **unpredictable**?



How to set up **new grid infrastructure** in congested areas?

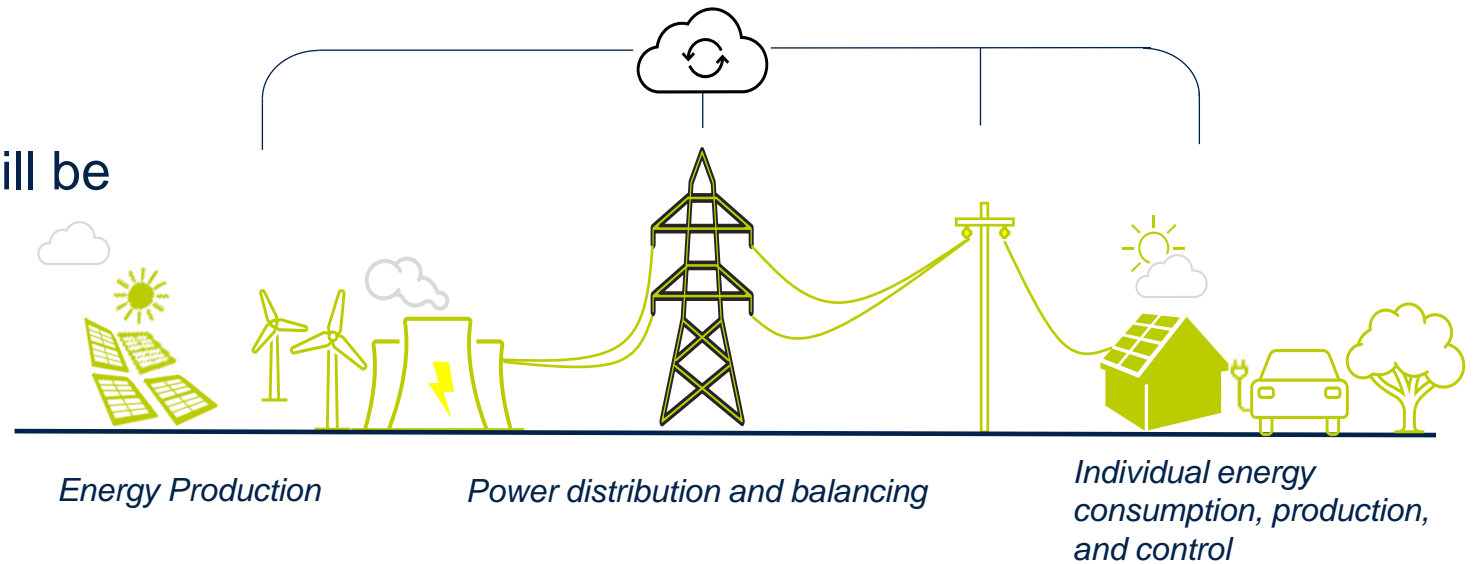


How to ensure a **reliable** supply to critical functions?



Secure & resilient power network

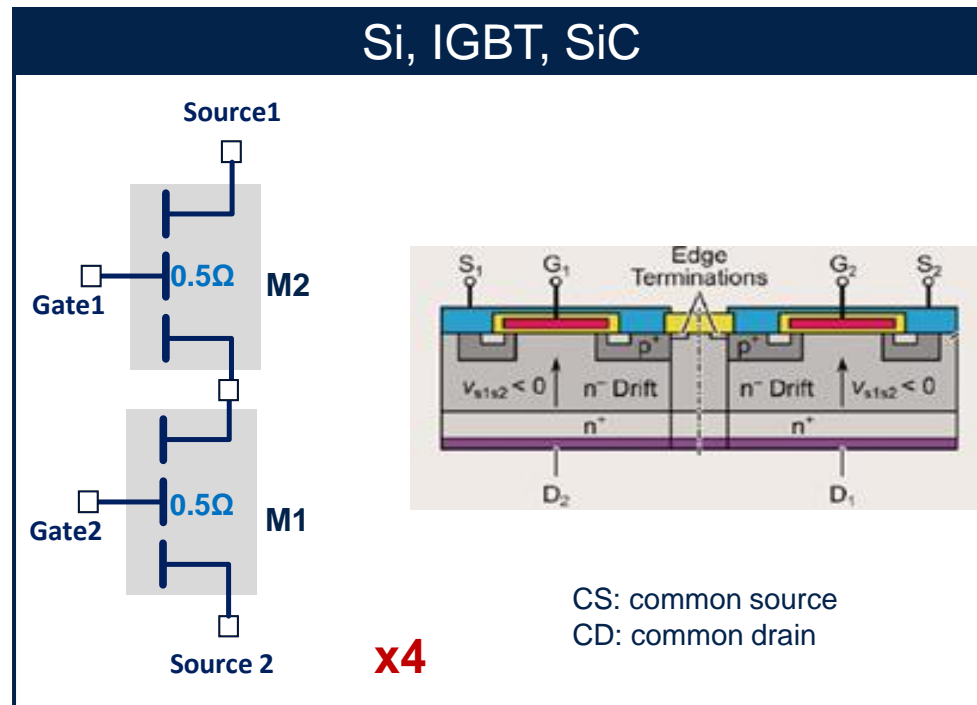
- Stationary energy storages: stabilize the network
- Easily deployable: EV batteries will be widely adopted
- Interconnected network from individual user / distribution / global and local production
- Immunity to cyber attack



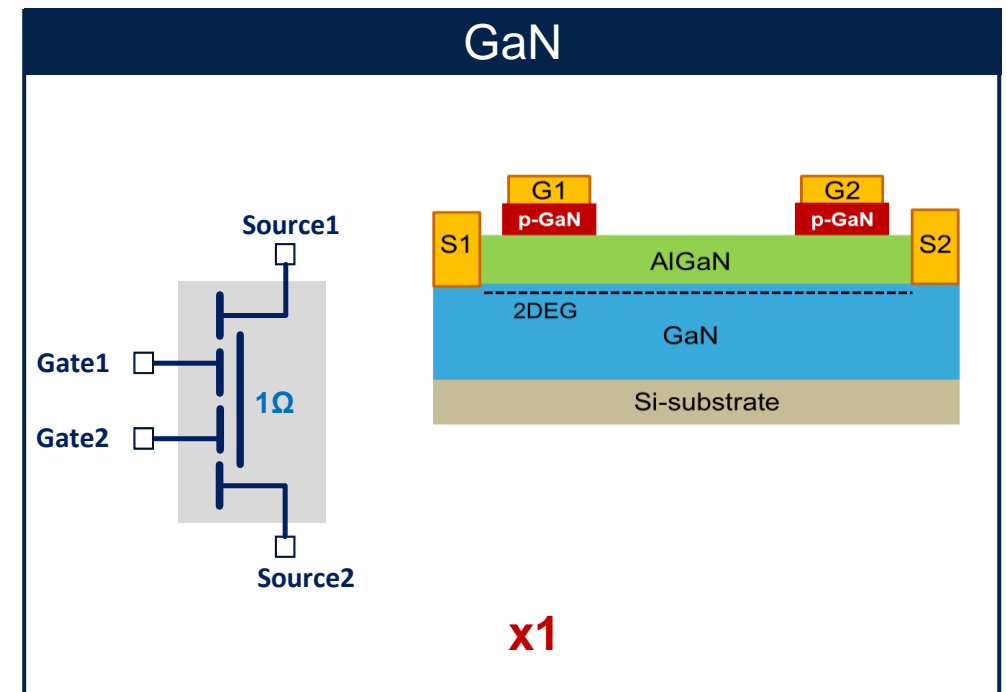
New applications require bidirectional power flow

Bidirectional switch

Bidirectional switches in CS or CD configuration with two separated drift regions



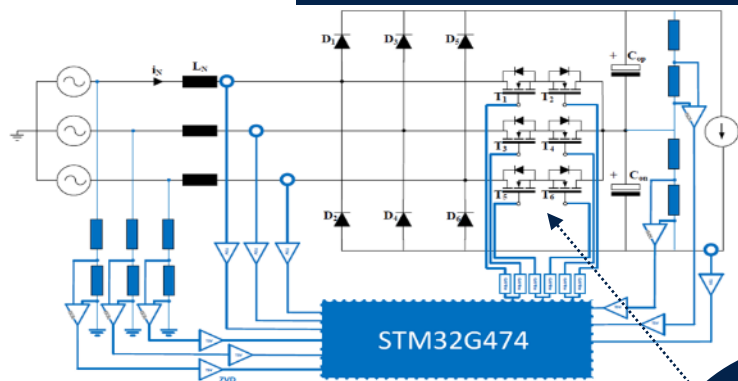
Bidirectional switches in CD configuration with shared drift region



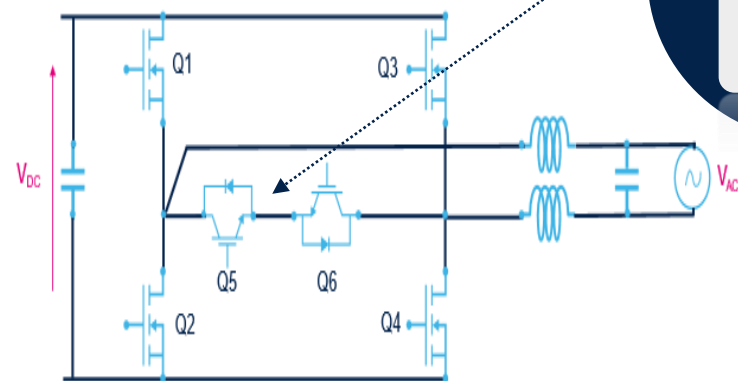
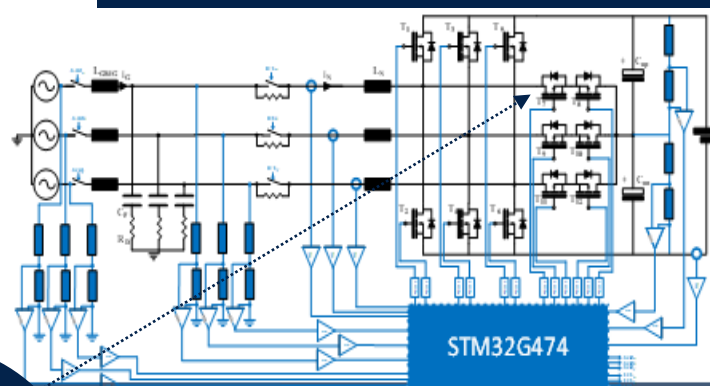
Monolithic BDR switch is a key feature of GaN technology

Bidirectional GaN to replace back-to-back switches

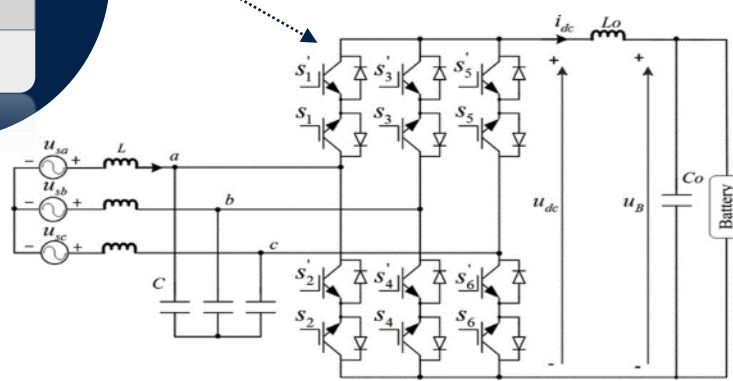
3L Vienna rectifier



3L T-Type bidirectional PFC



HERIC inverter

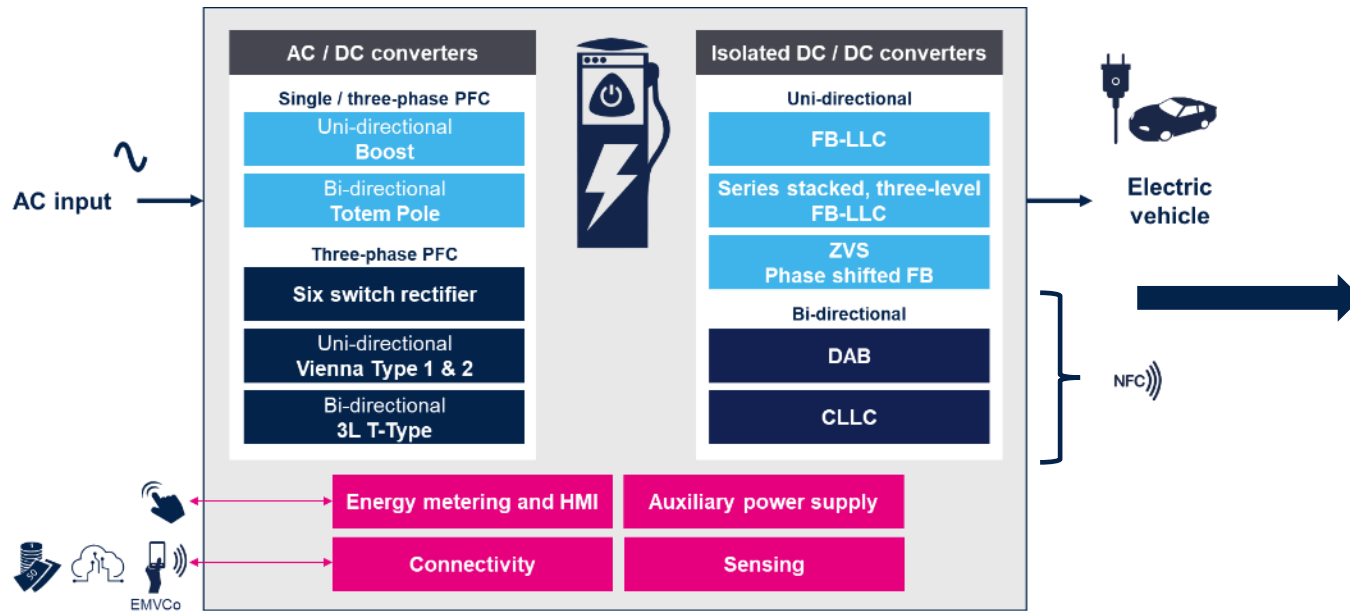
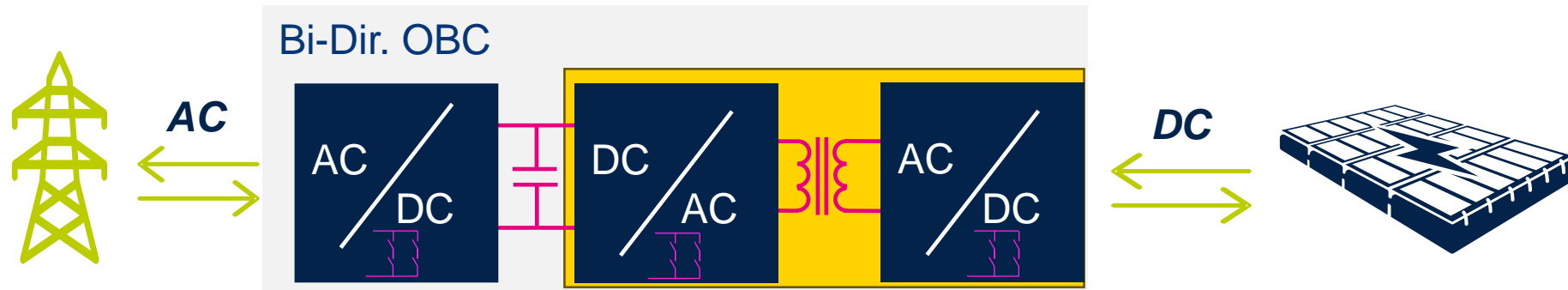


AC-DC-matrix converter



- Components reduction
- Higher frequency operation due to GaN
- Size reduction of passive components
- Increased power density
- System's cost reduction

Bidirectional GaN – On-board charger



Bidirectional GaN to enable:

- Simplified system, less passive and power switch components
- Higher system robustness and reliability
- Higher power density for even more space and weight saving

Motor control landscape

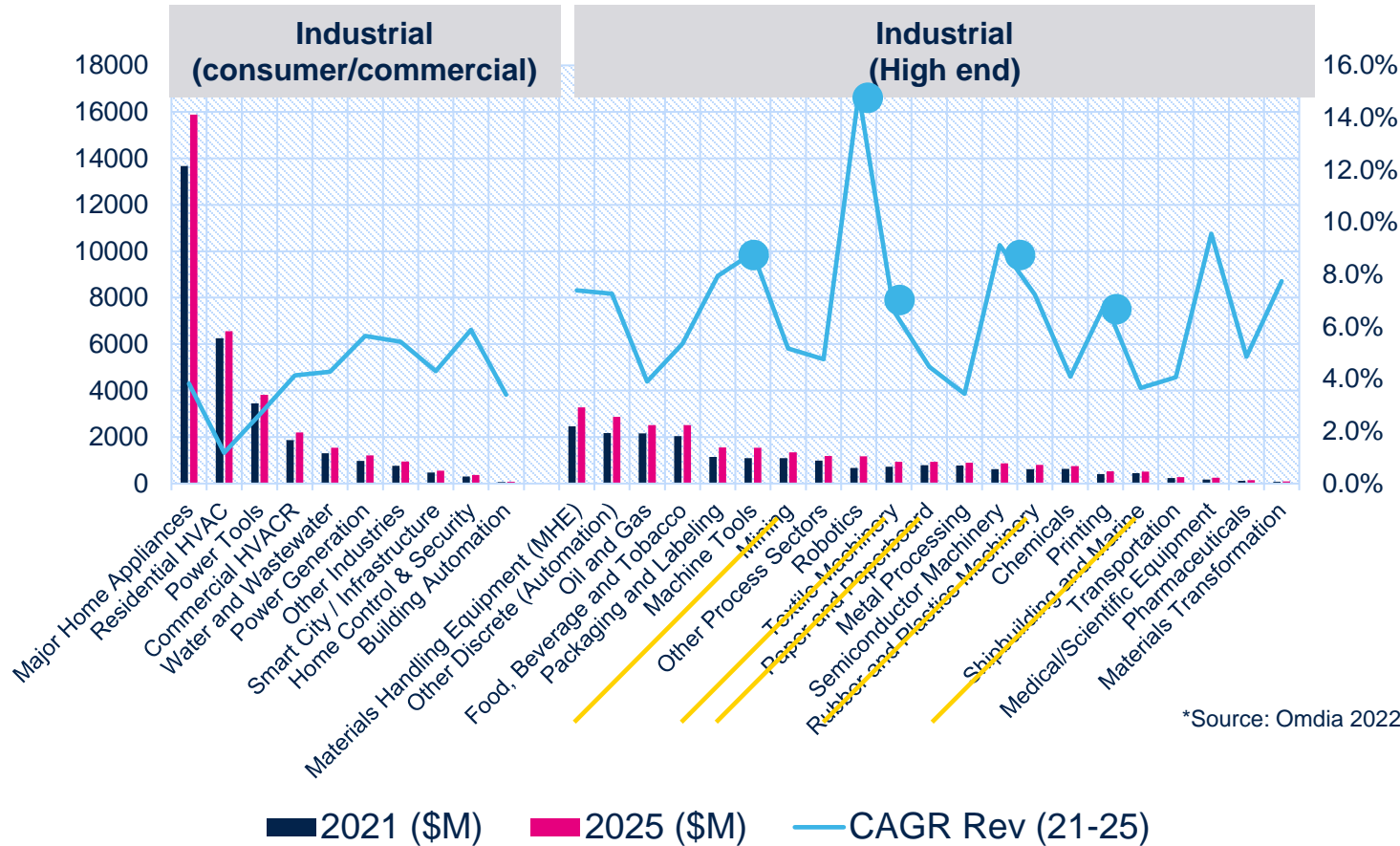
53% of total global electricity production is consumed by electric motors

**IEA Net Zero milestone
All industrial electrical motor sales are
best-in-class by 2035**

**20% gap to best-in-class technology
today**

Servo drives Top CAGR in high end industrial

Motor drive shipments (\$M) & CAGR 21-25 (%)*



*Source: Omdia 2022

Robotics
CAGR
14.9%



Semiconductor
machinery
CAGR 9.1%



Machine
tools
CAGR 8.8%



500 W high voltage motor drives based on GaN

GaN high voltage servo motor drive



Key features:

- GaN ready solution for motion control
- 10 V dV/dt both hard-on and hard-off
- Overcurrent protection integrated in the gate driver
- FOC supported
- Designed for 230 V AC mains
- HEMT GaN 650 V, 65 mΩ typ R_{DSon}

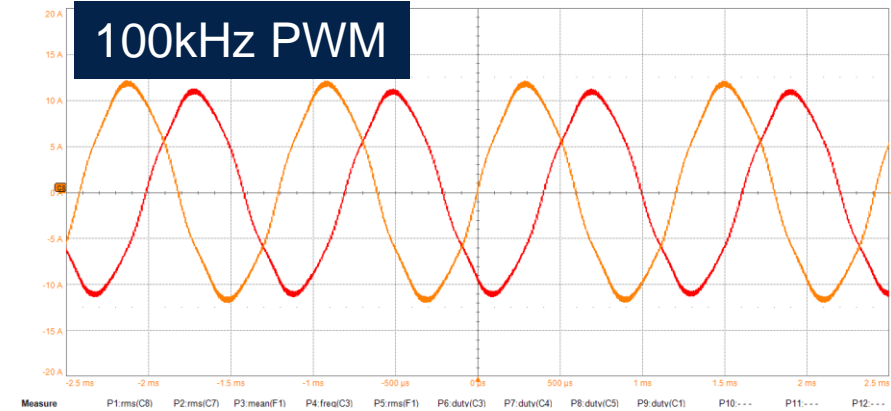
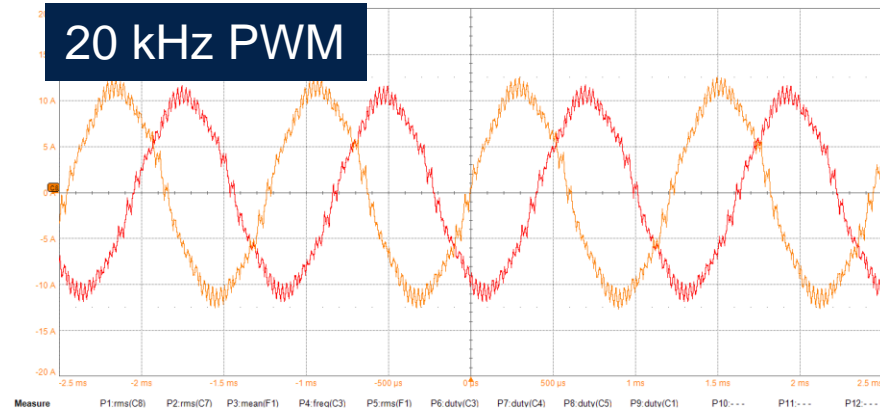
Specifications:

- 500 W+ max output power without cooling fan
- RS485 for absolute position encoder
- SPI, I²C
- Hall sensor & encoder

Applications

- Home appliances
- Servo drives
- High speed motors & tools
- Miniaturized motors

Overall efficiency improvement increasing the PWM frequency



Peaks	Frequency	Amplitude
1	750 Hz	6.5713 A
2	40.75 kHz	269.4 mA
3	39.25 kHz	248.8 mA
4	3.76 kHz	248.1 mA
5	21.50 kHz	159.0 mA
6	18.50 kHz	135.4 mA
7	122 Hz	115.7 mA
8	17.00 kHz	113.4 mA
9	23.00 kHz	102.3 mA
10	1.46 kHz	98.8 mA

Not producing active torque

Peaks	Frequency	Amplitude
1	750 Hz	6.6455 A
2	3.75 kHz	251.8 mA
3	199.24 kHz	85.2 mA
4	5.25 kHz	74.2 mA
5	98.50 kHz	44.4 mA
6	101.49 kHz	37.8 mA
7	103.00 kHz	31.1 mA
8	97.00 kHz	28.6 mA
9	196.24 kHz	11.4 mA
10	49.24 kHz	7.7 mA

	Si @20kHz	GaN @100kHz
Inverter efficiency	98.28%	98.68%
Motor efficiency		+4%
Overall efficiency		+4.12%

COP Test for HV fridge compressor



Compressor motor:

- Phase resistance: 10 Ω
- Ls: 200 mH



Power devices	Fpwm (kHz)	Nominal speed [rpm]	Cooling capacity [W]	Input power [W]	COP	COP increased
Leading solution STD8N60DM2	5	1200	65.793	34.681	1.897	
		3000	167.208	89.78	1.862	
		4500	232.425	145.847	1.594	
New ST GaN solution SGT120R65AL	5	1200	66.814	34.451	1.939	+2.2%
		3000	169.875	90.313	1.881	+1.0%
		4500	233.945	146.26	1.600	+0.3%
	8	1200	66.379	34.852	1.905	+0.4%
		3000	168.538	89.869	1.875	+0.6%
		4500	233.182	146.394	1.593	0

GaN technology adoption trends and opportunities

Penetration of existing markets



Consumer



Server

Improving value proposition

- Better figures of merits
- Lower system cost
- More system functionalities

From 15 to 240 W adapters



- Tiny USB Power Delivery
- LED lighting

Expansion into « new markets »



Automotive



Industrial

Providing performances

- High reliability
- Robust (short circuit, overload, ...)
- Advanced packaging
- Die integration (PM, IPM)

Auto On/Off board charger



- Higher efficiency
- Lower BOM cost

PSU data Server



- Hard switching applications
- Bridgeless Totem Pole
- DC-DC LLC

Substitution by alternatives



Defence



Energy



Aerospace

Challenging others

- High Voltage (900 - 1200 V)
- Vertical GaN
- Multicellular approach

Motor Control (Inverter)



- Fewer losses
- Less ripple torque
- Smaller filter

2020



2025



2030...



Our technology starts with You



Find out more at <http://www.st.com>

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